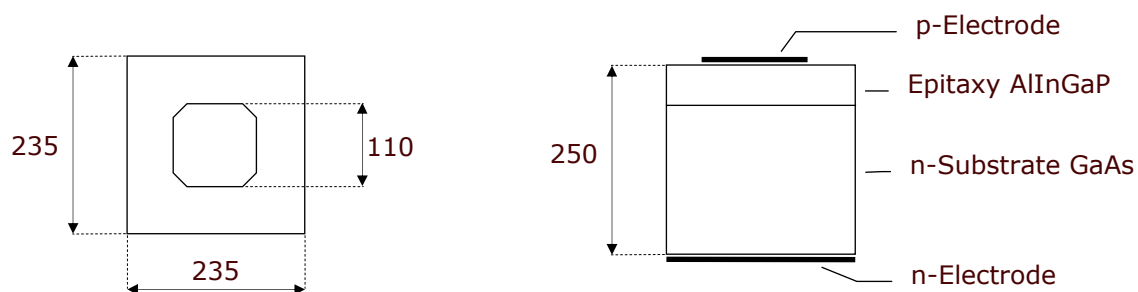


YELLOW

Item No.: 171282

1. This specification applies to AlInGaP / GaAs LED Chips
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

p-side (anode)	Au alloy or Al
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Chip thickness could also be 180 μm or 210 μm

Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	V_F	$I_F = 20 \text{ mA}$		2,10	2,40	V
Reverse current	I_R	$V_R = 5 \text{ V}$			10	μA
Luminous intensity *	I_V	$I_F = 10 \text{ mA}$		55		mcd
dom. wavelength	λ_D	$I_F = 20 \text{ mA}$		580		nm

* On request, wafers will be delivered according to luminous intensity classes
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top
2) back contact on top

6. Labeling

Type	Lot No.	I_V typ min max	Quantity
------	---------	-------------------------	----------